

**DL-3038-011****Index Guided AlGaInP Laser Diode****Overview**

DL-3038-011 is index guided 635 nm (Typ.) AlGaInP laser diode.

The low threshold current and short wavelength are achieved by a strained multiple quantum well active layer.

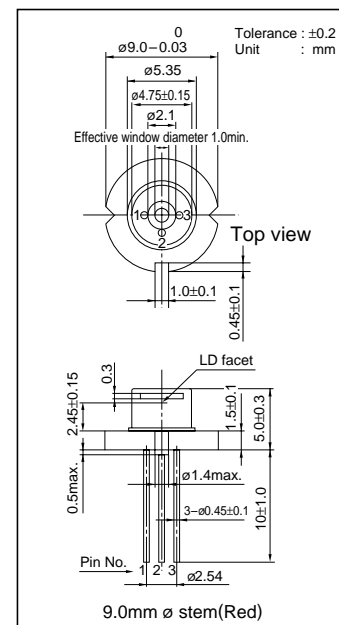
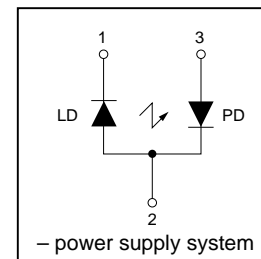
The lasing wavelength is the same as He-Ne gas lasers. DL-3038-011 is suitable for laser pointers.

Features

- Short wavelength : 635 nm (Typ.)
- High output power : 5 mW CW
- Low threshold current : $I_{th} = 40$ mA (Typ.)
- Low operating voltage : $V_{op} = 2.2$ V (Typ.)

Absolute Maximum Ratings at $T_c=25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Light Output	P_o	5	mW
Reverse Voltage	Laser PIN V_R	2	V
		30	
Operating Temperature	T_{opr}	-10 to +40	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

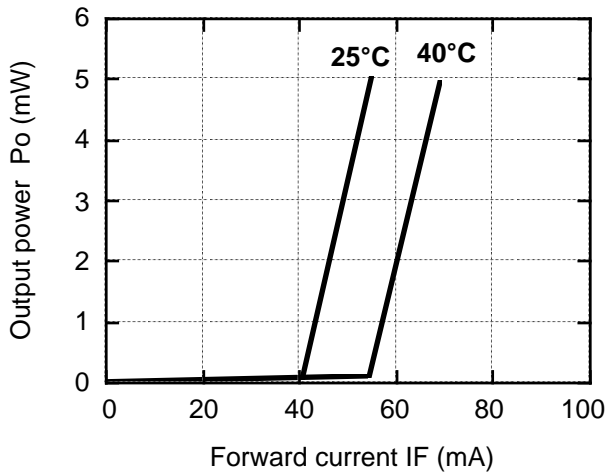
Package Dimensions**Electrical Connection****Electrical and Optical Characteristics at $T_c=25^\circ\text{C}$**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current	I_{th}	CW	-	40	70	mA
Operating Current	I_{op}	$P_o=5\text{mW}$	-	55	85	mA
Operating Voltage	V_{op}	$P_o=5\text{mW}$	-	2.2	2.4	V
Lasing Wavelength	λ_p	$P_o=5\text{mW}$	-	635	640	nm
Beam Divergence *)	Perpendicular	θ_{\perp}	25	35	40	deg.
	Parallel	θ_{\parallel}	6	8	10	deg.
Off Axis Angle	Perpendicular	$\Delta\theta_{\perp}$	-	-	± 3	deg.
	Parallel	$\Delta\theta_{\parallel}$	-	-	± 3	deg.
Differential Efficiency	dP_o/dI_{op}	-	0.1	0.3	-	mW/mA
Monitoring Output Current	I_m	$P_o=5\text{mW}$	0.05	0.2	-	mA
Astigmatism	A_s	$P_o=5\text{mW}$	-	8	-	μm

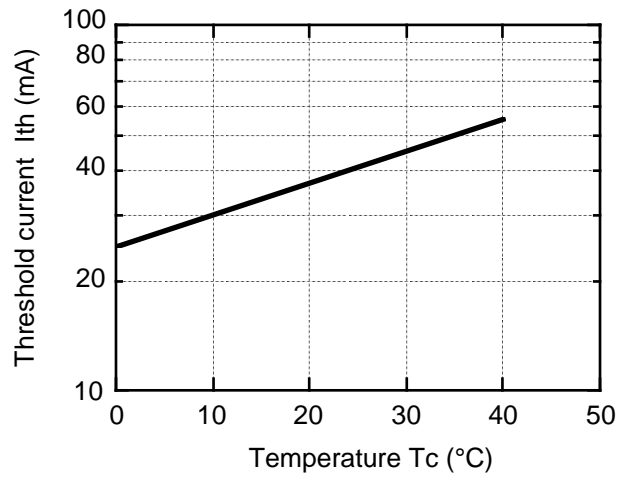
*) Full angle at half maximum note : The above product specifications are subject to change without notice.

Characteristics

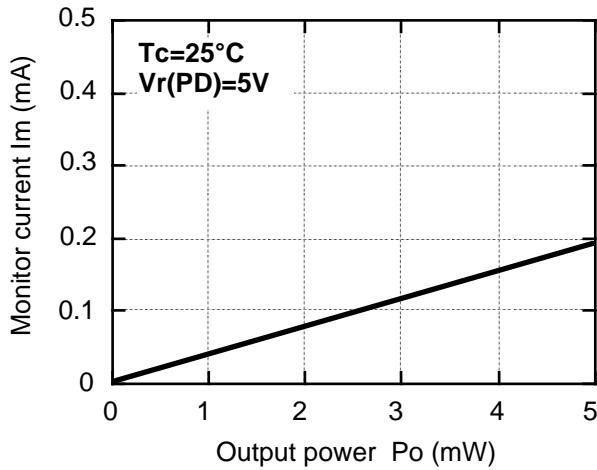
Output power vs. Forward current



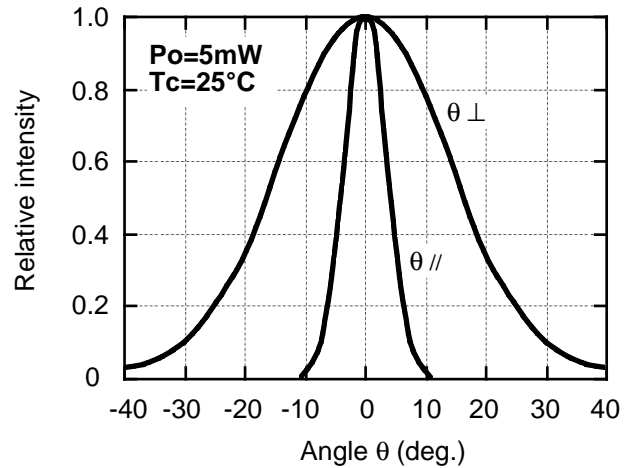
Threshold current vs. Temperature



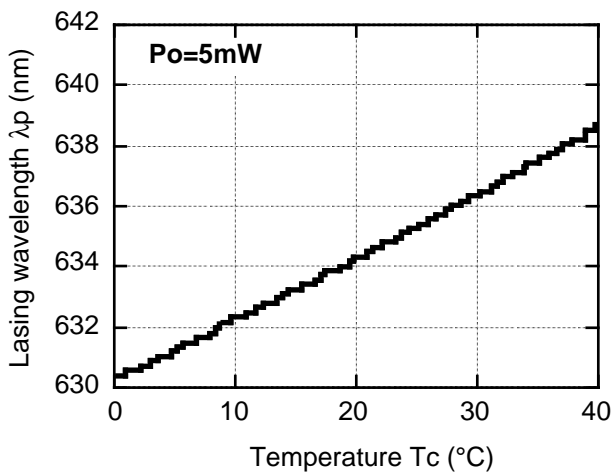
Monitor current vs. Output power



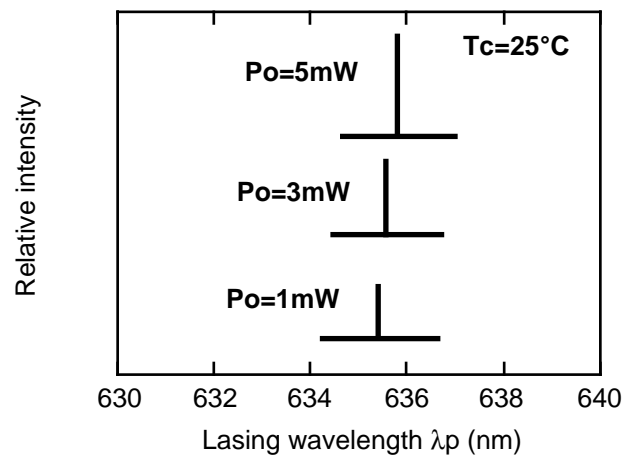
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



 **CAUTION**

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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by ; **Tottori SANYO Electric Co., Ltd.**
Electronics Device Bussiness Headquarters LED Division
5-318, Tachikawa-cho, Tottori City, 680-8634 Japan
TEL: +81-857-21-2137 FAX: +81-857-21-2161